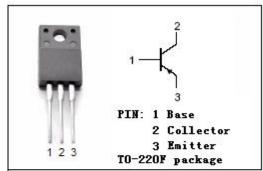




isc Silicon PNP Power Transistor

DESCRIPTION

- · Collector-Emitter Breakdown Voltage-
 - : $V_{(BR)CEO}$ = -80V(Min)
- · Low Collector Saturation Voltage-
 - : $V_{CE(sat)}$ = -0.5V(Max)@ (I_C= -4A, I_B= -0.4A)
- Complement to Type 2SD2203
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

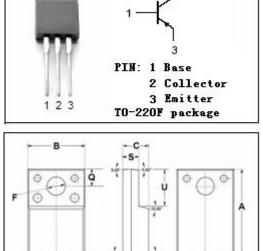


APPLICATIONS





SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	-90	V
V _{CEO}	Collector-Emitter Voltage	-80	V
V _{EBO}	Emitter-Base Voltage	-6	V
Ic	Collector Current-Continuous	-7	А
I _{CM}	Collector Current-Pulse	-12	А
Pc	Collector Power Dissipation @T _a =25℃	2	\A/
	Collector Power Dissipation @T _C =25°C	30	W
TJ	Junction Temperature	150	$^{\circ}$
T _{stg}	Storage Temperature	-55~150	$^{\circ}$ C



	mm	
DIM	MIN	MAX
Α	14.95	15.05
В	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
Н	3.70	3.90
5	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Ö	2.70	2.90
R	2.20	2.40
S	2.65	2.85
Ü	6.40	6.60



isc Silicon PNP Power Transistor

2SB1455

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

Tj=25 [°] C unless otherwise specified							
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -1mA; R _{BE} = ∞	-80			V	
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -1mA; I _E = 0	-90			V	
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA; I _C = 0	-6			V	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -4A; I _B = -0.4A			-0.5	V	
І _{сво}	Collector Cutoff Current	V _{CB} = -80V; I _E = 0			-100	μ А	
I _{EBO}	Emitter Cutoff Current	V _{EB} = -4V; I _C = 0			-100	μ А	
h _{FE-1}	DC Current Gain	Ic= -1A; V _{CE} = -2V	70		280		
h _{FE-2}	DC Current Gain	I _C = -4A; V _{CE} = -2V	30				
f _T	Current-Gain—Bandwidth Product	I _C = -1A; V _{CE} = -5V		20		MHz	
Switching Times							
t _{on}	Turn-on Time			0.2		μ S	
t _{stg}	Storage Time	V_{CC}^{-} -50V, R_L = 25 Ω , I_C = -2A; I_{B1} = - I_{B2} = -0.2A,		0.7		μS	
t _f	Fall Time			0.2		μS	

♦ h_{FE-1} Classifications

Q	R	S
70-140	100-200	140-280



isc Silicon PNP Power Transistor

2SB1455

Notice:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

3

